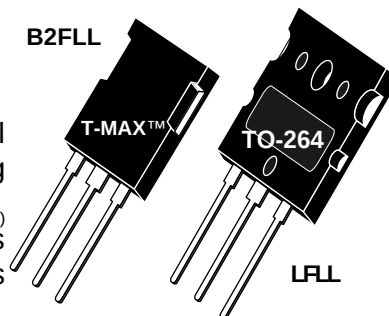
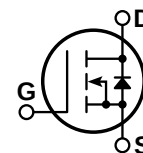


POWER MOS 7® FREDFET

Power MOS 7® is a new generation of low loss, high voltage, N-Channel enhancement mode power MOSFETS. Both conduction and switching losses are addressed with Power MOS 7® by significantly lowering $R_{DS(ON)}$ and Q_g . Power MOS 7® combines lower conduction and switching losses along with exceptionally fast switching speeds inherent with APT's patented metal gate structure.



- Lower Input Capacitance
- Lower Miller Capacitance
- Lower Gate Charge, Q_g
- Increased Power Dissipation
- Easier To Drive
- Popular T-MAX™ or TO-264 Package
- **FAST RECOVERY BODY DIODE**



MAXIMUM RATINGS

All Ratings: $T_C = 25^\circ\text{C}$ unless otherwise specified.

Symbol	Parameter	APT30M30	UNIT
V_{DSS}	Drain-Source Voltage	300	Volts
I_D	Continuous Drain Current @ $T_C = 25^\circ\text{C}$ ⑤	100	Amps
I_{DM}	Pulsed Drain Current ①	415	
V_{GS}	Gate-Source Voltage Continuous	± 30	Volts
V_{GSM}	Gate-Source Voltage Transient	± 40	
P_D	Total Power Dissipation @ $T_C = 25^\circ\text{C}$	694	Watts
	Linear Derating Factor	5.56	W/°C
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to 150	°C
T_L	Lead Temperature: 0.063" from Case for 10 Sec.	300	
I_{AR}	Avalanche Current ① (Repetitive and Non-Repetitive)	100	Amps
E_{AR}	Repetitive Avalanche Energy ①	50	mJ
E_{AS}	Single Pulse Avalanche Energy ④	3000	

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage ($V_{GS} = 0V, I_D = 250\mu A$)	300			Volts
$I_{D(on)}$	On State Drain Current ② ($V_{DS} > I_{D(on)} \times R_{DS(on)}$ Max, $V_{GS} = 10V$)	100			Amps
$R_{DS(on)}$	Drain-Source On-State Resistance ② ($V_{GS} = 10V, 50A$)			0.030	Ohms
I_{DSS}	Zero Gate Voltage Drain Current ($V_{DS} = 300V, V_{GS} = 0V$)			250	μA
	Zero Gate Voltage Drain Current ($V_{DS} = 240V, V_{GS} = 0V, T_C = 125^\circ\text{C}$)			1000	
I_{GSS}	Gate-Source Leakage Current ($V_{GS} = \pm 30V, V_{DS} = 0V$)			± 100	nA
$V_{GS(th)}$	Gate Threshold Voltage ($V_{DS} = V_{GS}, I_D = 2.5mA$)	3		5	Volts

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

APT Website - <http://www.advancedpower.com>

DYNAMIC CHARACTERISTICS

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
C_{iss}	Input Capacitance	$V_{GS} = 0V$ $V_{DS} = 25V$ $f = 1\text{ MHz}$		7030		pF
C_{oss}	Output Capacitance			1894		
C_{rss}	Reverse Transfer Capacitance			111		
Q_g	Total Gate Charge ^③	$V_{GS} = 10V$ $V_{DD} = 150V$ $I_D = 100A @ 25^\circ C$		139		nC
Q_{gs}	Gate-Source Charge			41		
Q_{gd}	Gate-Drain ("Miller") Charge			68		
$t_{d(on)}$	Turn-on Delay Time	$V_{GS} = 15V$ $V_{DD} = 150V$ $I_D = 100A @ 25^\circ C$ $R_G = 0.6\Omega$		15		ns
t_r	Rise Time			22		
$t_{d(off)}$	Turn-off Delay Time			35		
t_f	Fall Time			8		

SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
I_S	Continuous Source Current (Body Diode)			100	Amps
I_{SM}	Pulsed Source Current ^① (Body Diode)			415	
V_{SD}	Diode Forward Voltage ^② ($V_{GS} = 0V$, $I_S = -100A$)			1.3	Volts
dv/dt	Peak Diode Recovery dv/dt ^⑥			8	V/ns
t_{rr}	Reverse Recovery Time ($I_S = -100A$, $di/dt = 100A/\mu s$)	$T_j = 25^\circ C$		250	ns
		$T_j = 125^\circ C$		500	
Q_{rr}	Reverse Recovery Charge ($I_S = -100A$, $di/dt = 100A/\mu s$)	$T_j = 25^\circ C$		1.4	μC
		$T_j = 125^\circ C$		4.9	
I_{RRM}	Peak Recovery Current ($I_S = -100A$, $di/dt = 100A/\mu s$)	$T_j = 25^\circ C$		14	Amps
		$T_j = 125^\circ C$		25	

THERMAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case			0.18	$^\circ C/W$
$R_{\theta JA}$	Junction to Ambient			40	

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② Pulse Test: Pulse width < 380 μs , Duty Cycle < 2%

③ See MIL-STD-750 Method 3471

④ Starting $T_j = +25^\circ C$, $L = .60mH$, $R_G = 25\Omega$, Peak $I_L = 100A$

⑤ The maximum current is limited by lead temperature

⑥ dv/dt numbers reflect the limitations of the test circuit rather than the device itself. $I_S \leq -I_{B[Cont]}$ $di/dt \leq 700A/\mu s$ $V_R \leq V_{DSS}$ $T_j \leq 150^\circ C$

APT Reserves the right to change, without notice, the specifications and information contained herein.

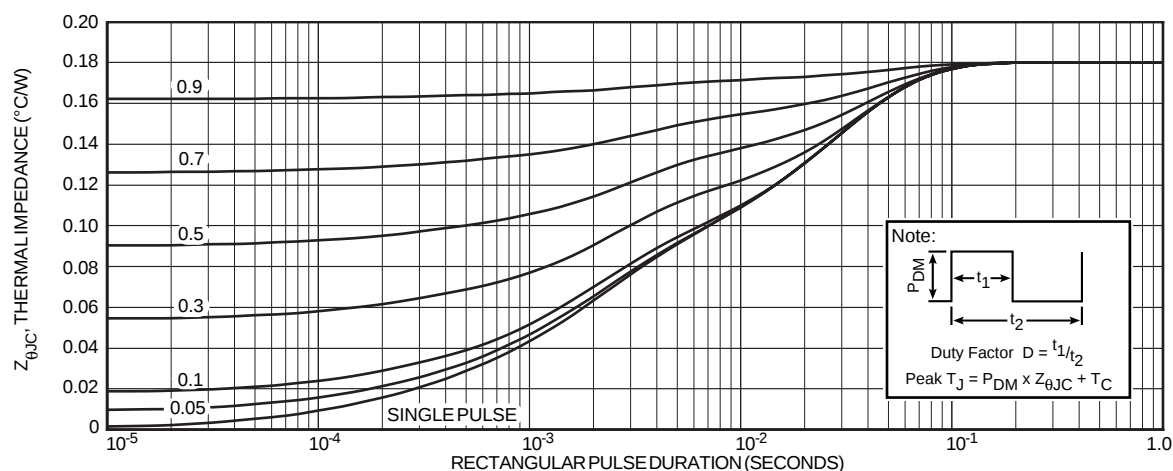


FIGURE 1, MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs PULSE DURATION

Typical Performance Curves

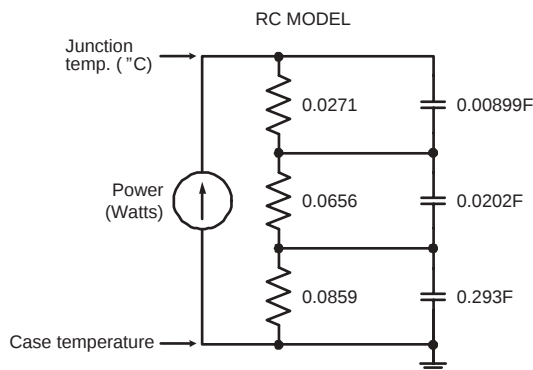


FIGURE 2, TRANSIENT THERMAL IMPEDANCE MODEL

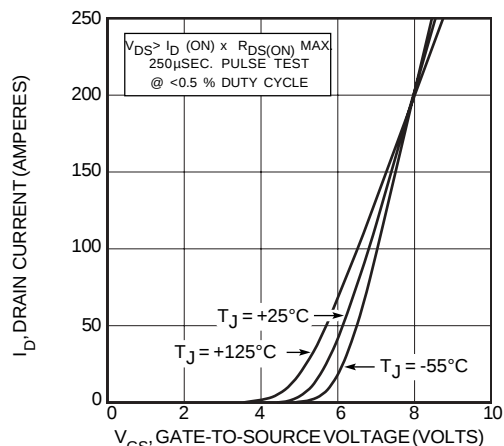


FIGURE 4, TRANSFER CHARACTERISTICS

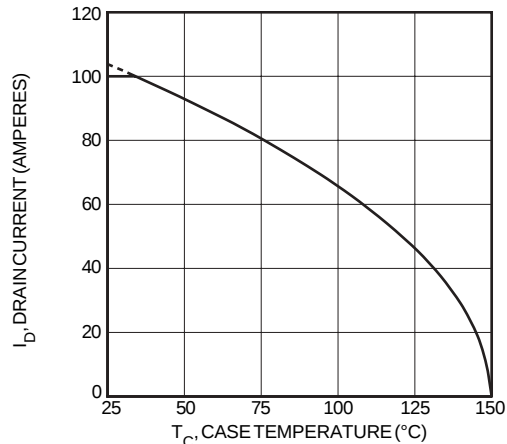


FIGURE 6, MAXIMUM DRAIN CURRENT vs CASE TEMPERATURE

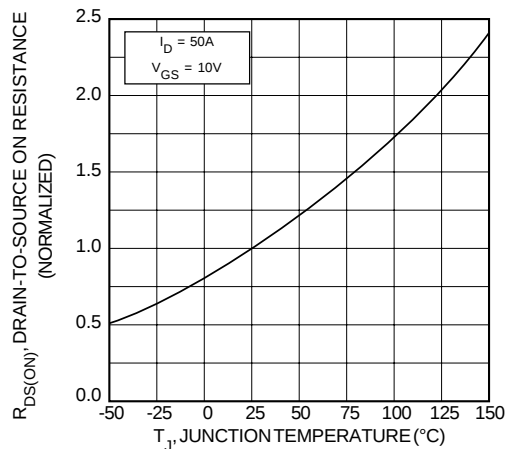


FIGURE 8, $R_{DS(\text{ON})}$ vs. TEMPERATURE

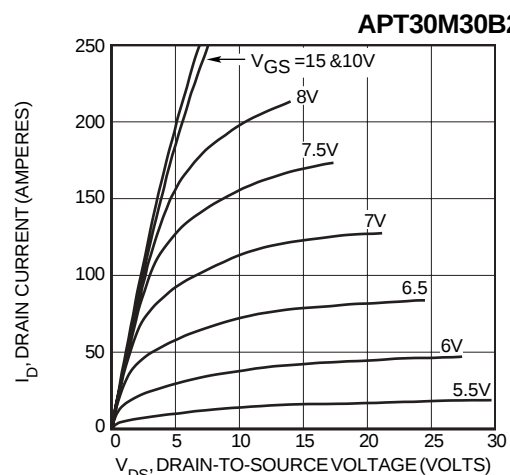


FIGURE 3, LOW VOLTAGE OUTPUT CHARACTERISTICS

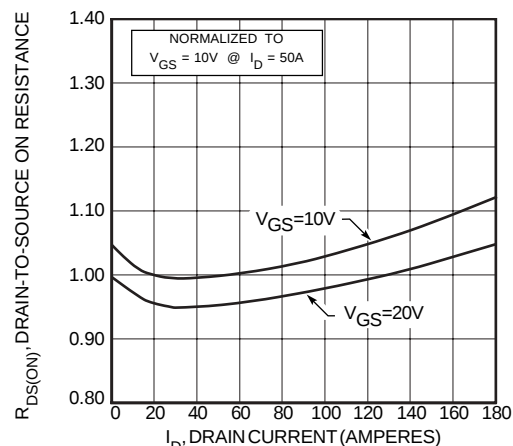


FIGURE 5, $R_{DS(\text{ON})}$ vs DRAIN CURRENT

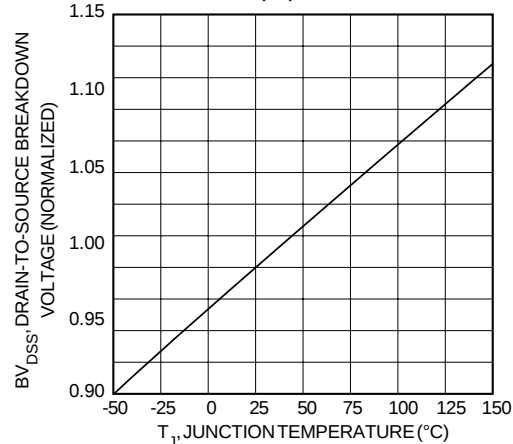


FIGURE 7, BREAKDOWN VOLTAGE vs TEMPERATURE

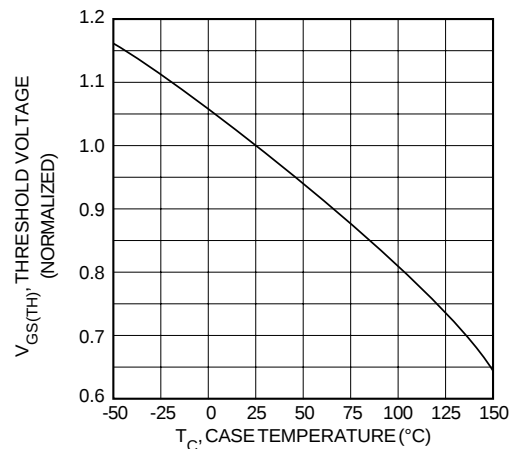


FIGURE 9, THRESHOLD VOLTAGE vs TEMPERATURE

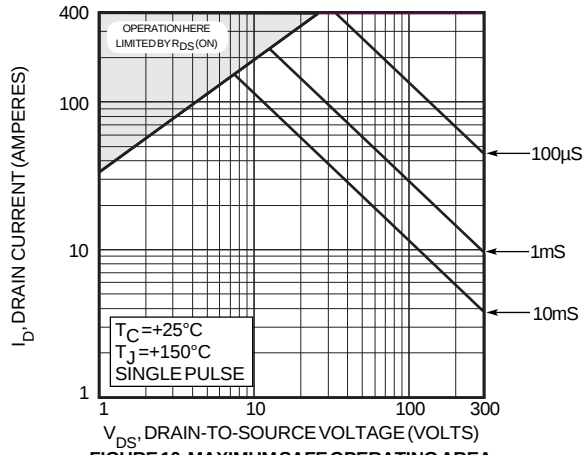


FIGURE 10, MAXIMUM SAFE OPERATING AREA

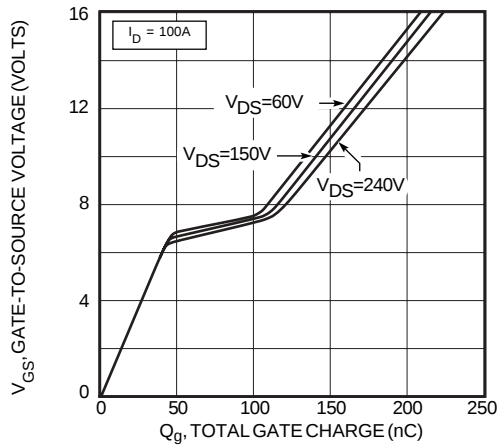


FIGURE 12, GATE CHARGE vs GATE-TO-SOURCE VOLTAGE

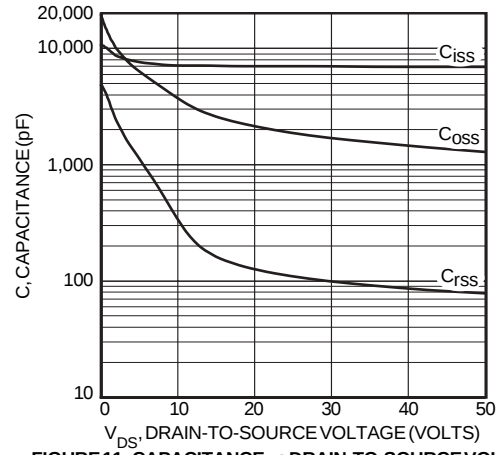


FIGURE 11, CAPACITANCE vs DRAIN-TO-SOURCE VOLTAGE

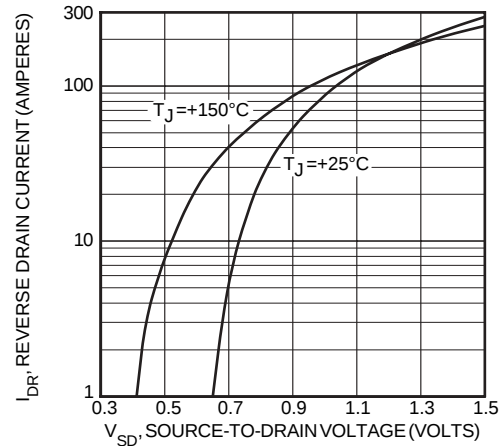
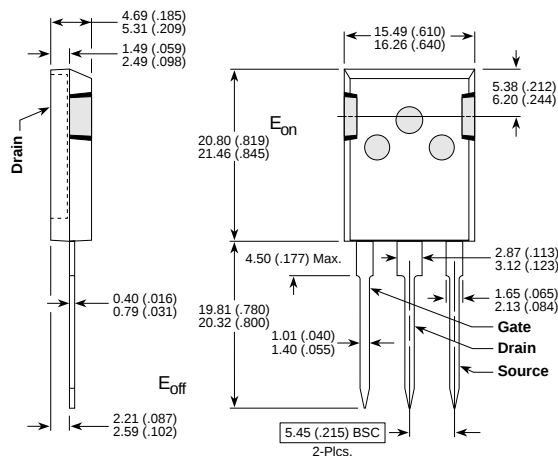


FIGURE 13, SOURCE-DRAIN DIODE FORWARD VOLTAGE

T-MAX™ (B2) Package Outline

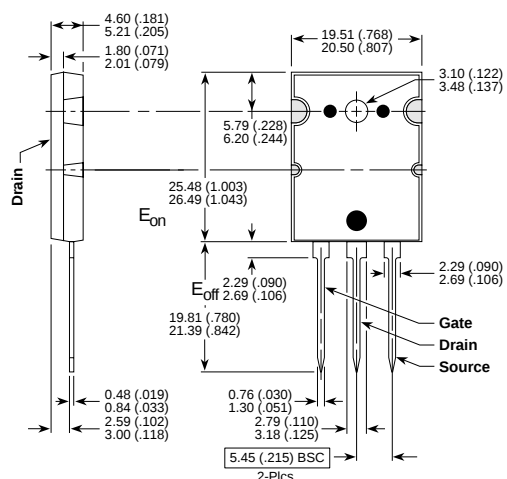


These dimensions are equal to the TO-247 without the mounting hole.

Dimensions in Millimeters and (Inches)

APT's devices are covered by one or more of the following U.S. patents: 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058

TO-264 (L) Package Outline



Dimensions in Millimeters and (Inches)

5,182,234 5,019,522 5,262,336 5,231,474 5,434,095 5,528,058